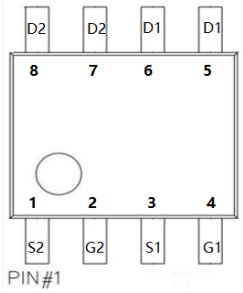
Dual N-Channel Enhancement Mode Field Effect Transistor

Features

V_{DS} (V) = 20V
I_D = 7A
$R_{DS(ON)}$ < 26mΩ (V_{GS} = 4.5V)
$R_{DS(ON)}$ < 33mΩ (V_{GS} = 2.5V)
$R_{DS(ON)}$ < 42mΩ (V_{GS} = 1.8V)



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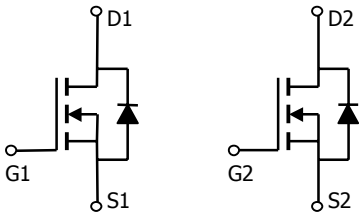

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current [A]	T_A=25°C	I_D	7	A
	T_A=70°C		6	
Pulsed Drain Current [B]		I_{DM}	40	
Power Dissipation	T_A=25°C	P_D	2	W
	T_A=70°C		1.44	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	48	62.5	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		74	110	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	35	40	°C/W

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Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA, V_{GS}=0V	20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=16V, V_{GS}=0V			1	μA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±8V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250μA	0.3	0.5	0.8	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V, I_D=7A		21.6	26	mΩ
		T_J=125°C		29.2	36	
		V_{GS}=2.5V, I_D=5A		26.4	33	mΩ
		V_{GS}=1.8V, I_D=4A		33.3	42	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=5A		22		S
V_{SD}	Diode Forward Voltage	I_S=1A		0.76	1	V
I_S	Maximum Body-Diode Continuous Current				3	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=10V, f=1MHz		1050		pF
C_{oss}	Output Capacitance			163		pF
C_{rss}	Reverse Transfer Capacitance			129		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		4		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=10V, I_D=7A		15.2		nC
Q_{gs}	Gate Source Charge			1		nC
Q_{gd}	Gate Drain Charge			4		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=5V, V_{DS}=10V, R_L=1.5Ω, R_{GEN}=3Ω		6.5		ns
t_r	Turn-On Rise Time			9		ns
$t_{D(off)}$	Turn-Off DelayTime			56.5		ns
t_f	Turn-Off Fall Time			13.2		ns
t_{rr}	Body Diode Reverse Recovery time	I_F=5A, dI/dt=100A/μs		21		ns
Q_{rr}	Body Diode Reverse Recovery charge	I_F=5A, dI/dt=100A/μs		7.1		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t≤ 10s thermal resistance rating.
B: Repetitive rating, pulse width limited by junction temperature.
C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
D. The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5% max.
E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

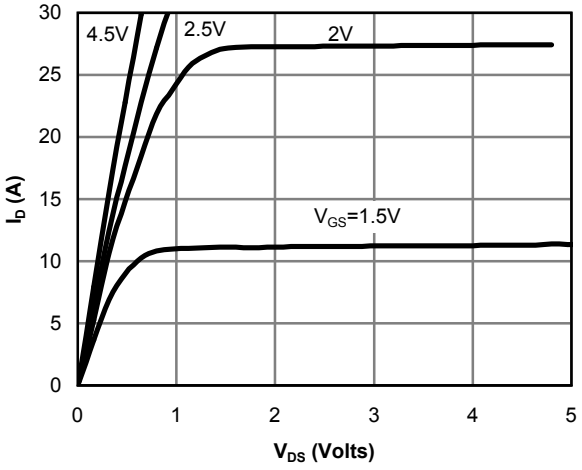

Fig 1: On-Region Characteristics

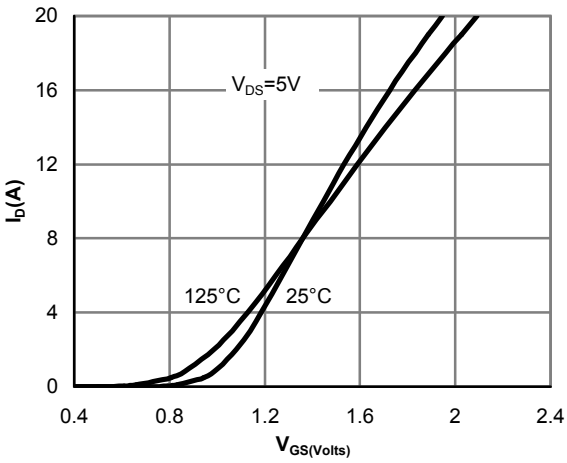

Figure 2: Transfer Characteristics

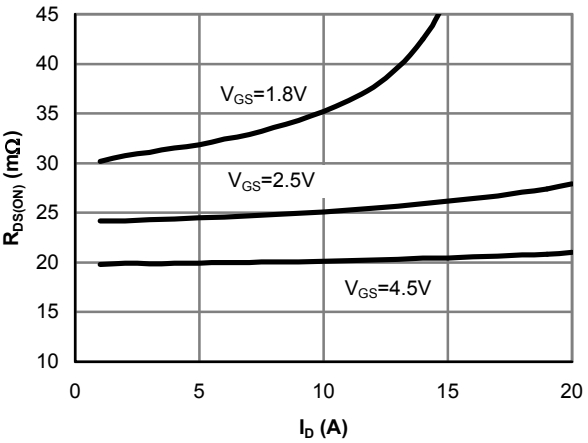

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

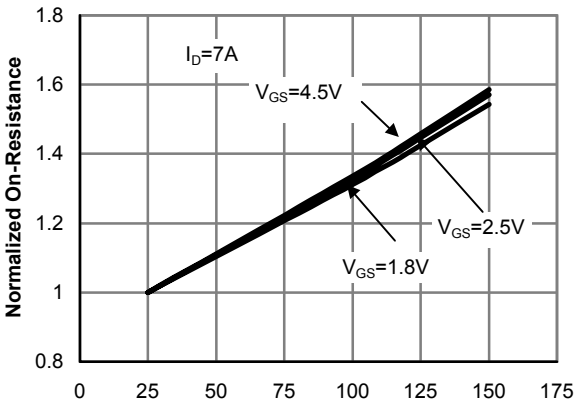

Figure 4: On-Resistance vs. Junction Temperature

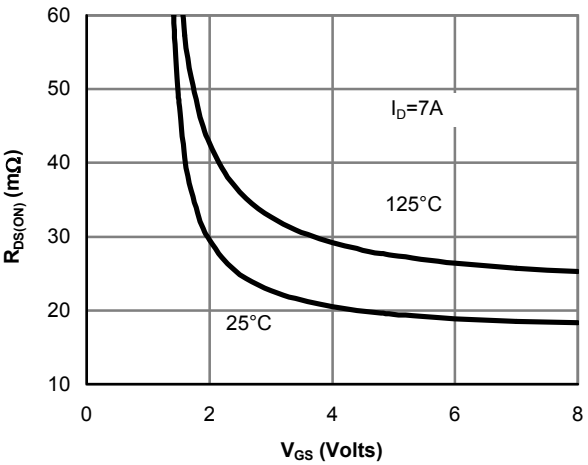

Figure 5: On-Resistance vs. Gate-Source Voltage

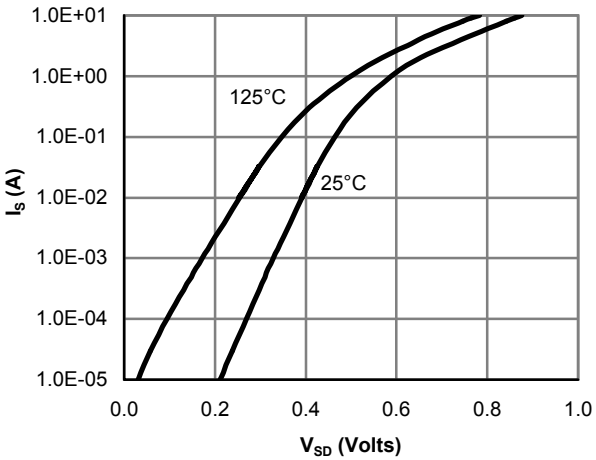

Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

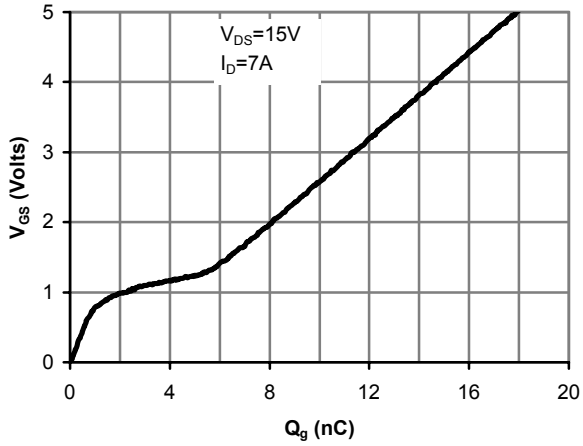

Figure 7: Gate-Charge Characteristics

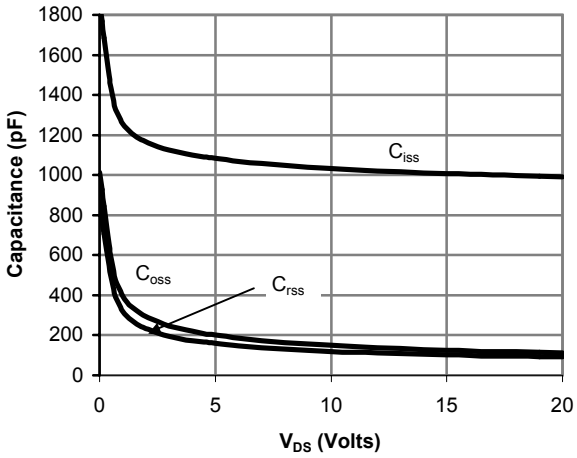

Figure 8: Capacitance Characteristics

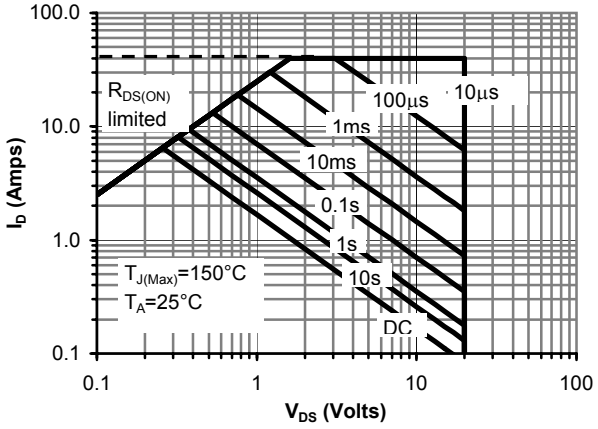

Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

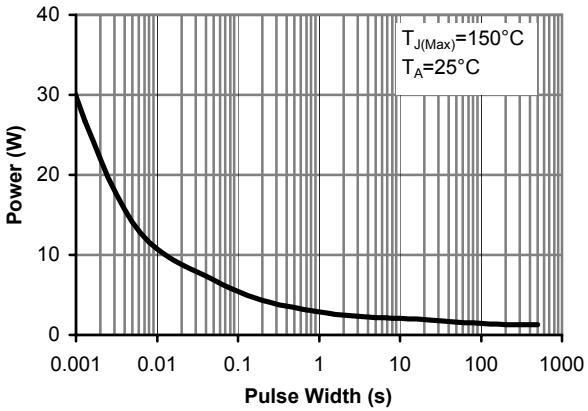

Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

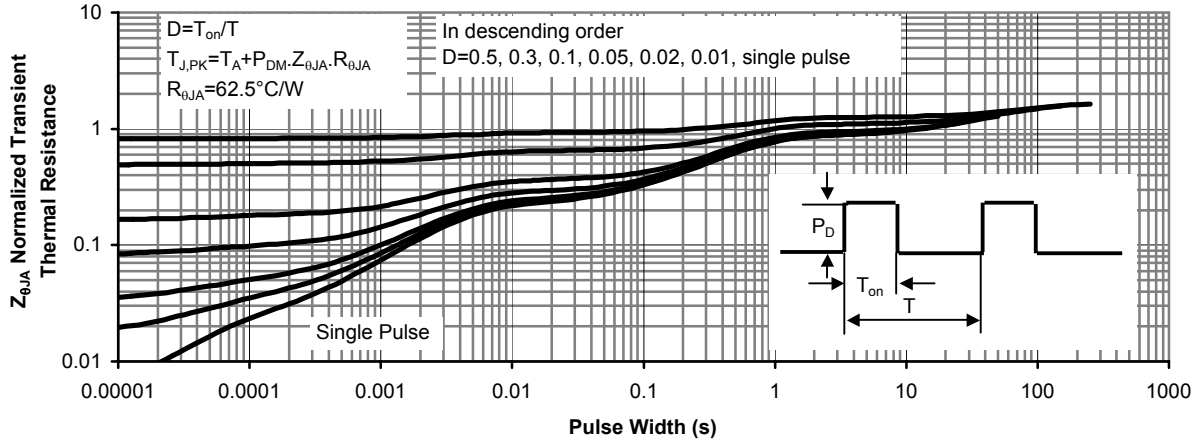

Figure 11: Normalized Maximum Transient Thermal Impedance

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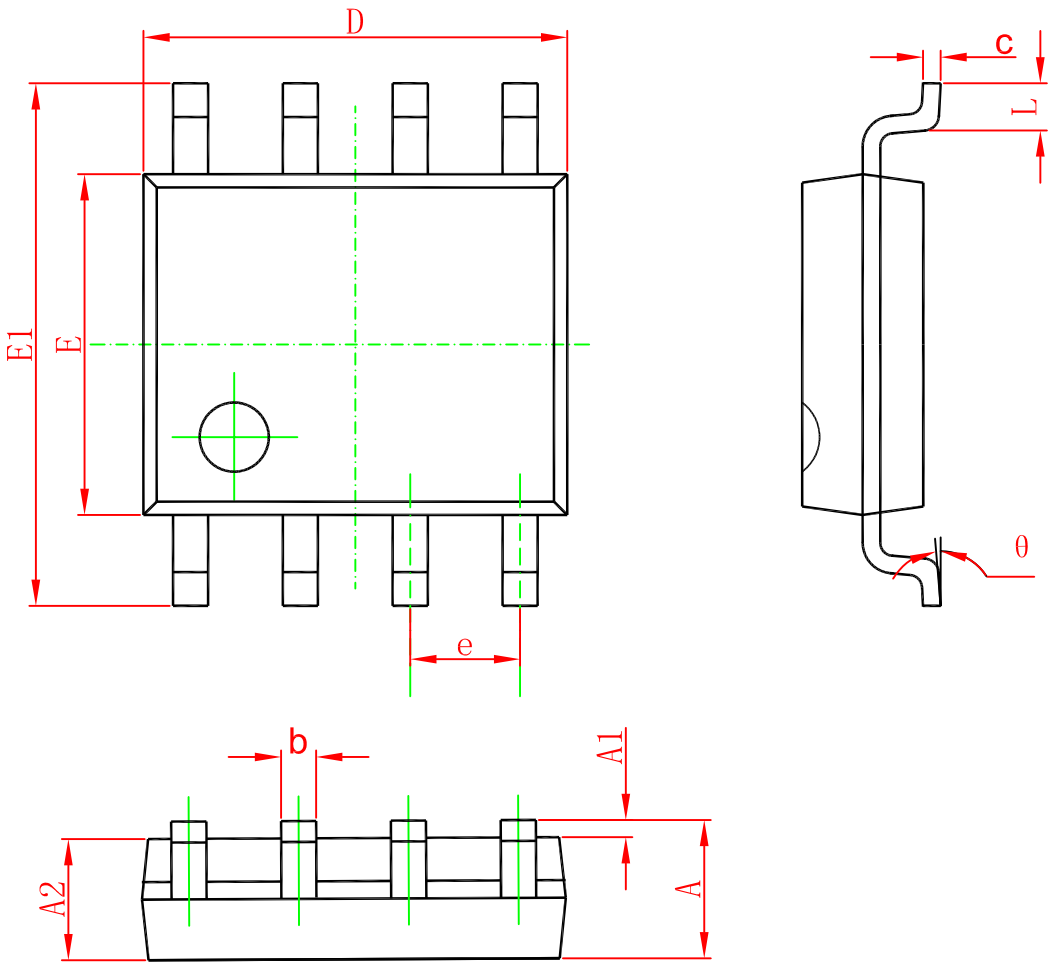
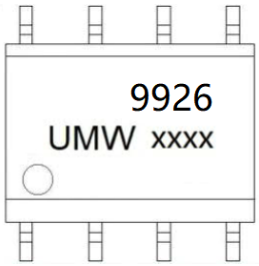


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Marking



("xxxx"代表年份周期)

Ordering information

Order Code	Package	Baseqty	Deliverymode
UMW CEM9926A	SOP-8	3000	Tape and reel